



FX501

PNP Epitaxial Planar Silicon Transistor

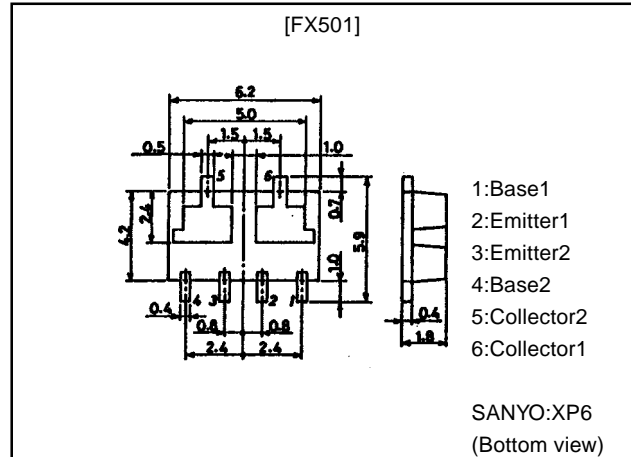
High-Current Switching Applications

Features

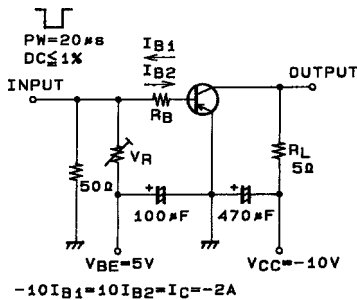
- Composite type with 2 PNP transistors contained in one package, facilitating high-density mounting.
- The FX501 houses two chips, each being equivalent to the 2SB1205, in one package.
- Matched pair characteristics.

Package Dimensions

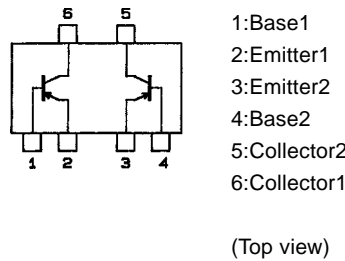
unit:mm
2118



Switching Time Test Circuit



Electrical Connection



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		-25	V
Collector-to-Emitter Voltage	V_{CEO}		-20	V
Emitter-to-Base Voltage	V_{EBO}		-5	V
Collector Current	I_C		-5	A
Collector Current (Pulse)	I_{CP}		-8	A
Base Current	I_B		-1	A
Collector Dissipation	P_C	Mounted on ceramic board (750mm ² ×0.8mm) 1 unit	1.5	W
Total Dissipation	P_T	Mounted on ceramic board (750mm ² ×0.8mm)	2	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-50 to +150	°C

· Marking:501

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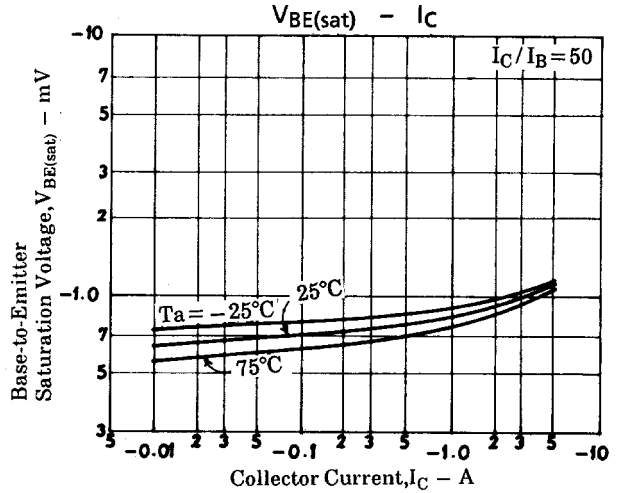
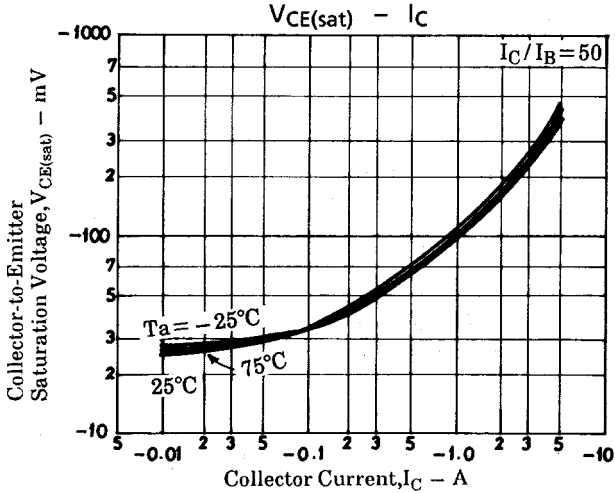
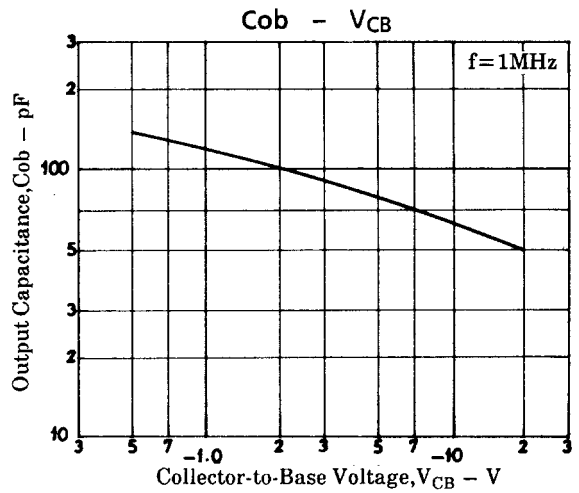
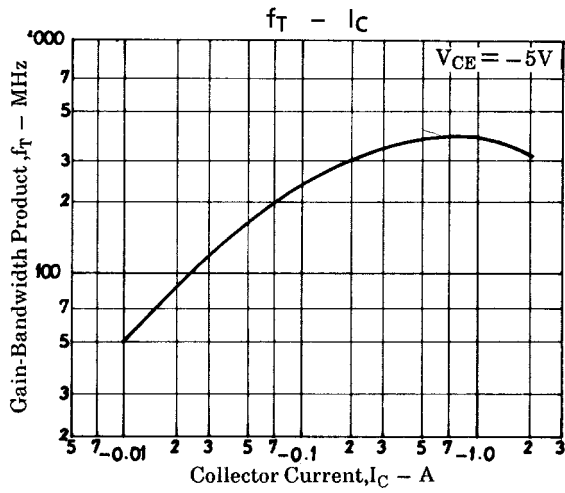
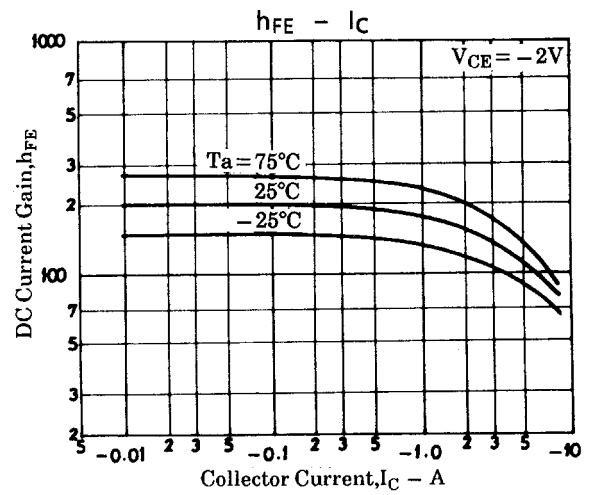
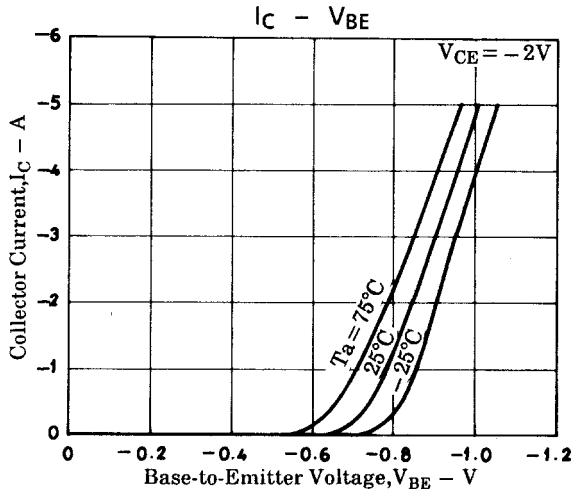
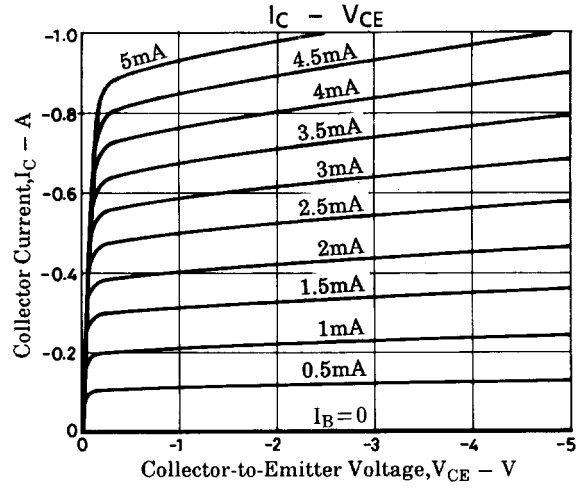
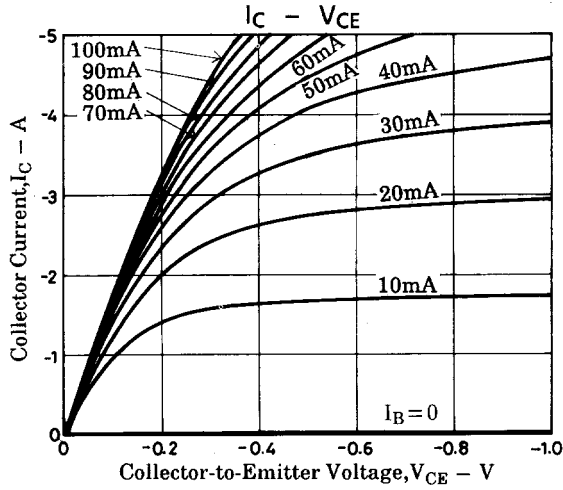
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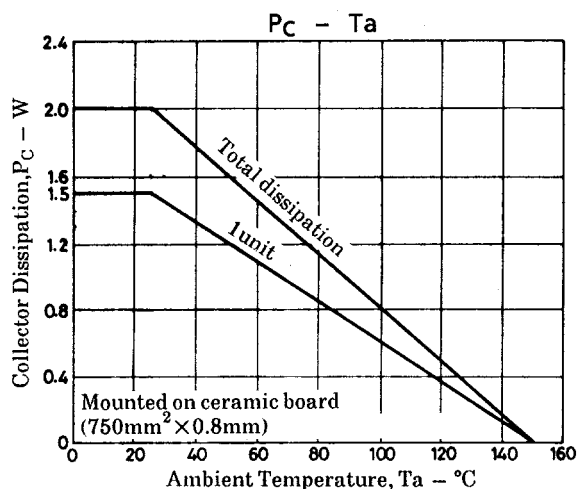
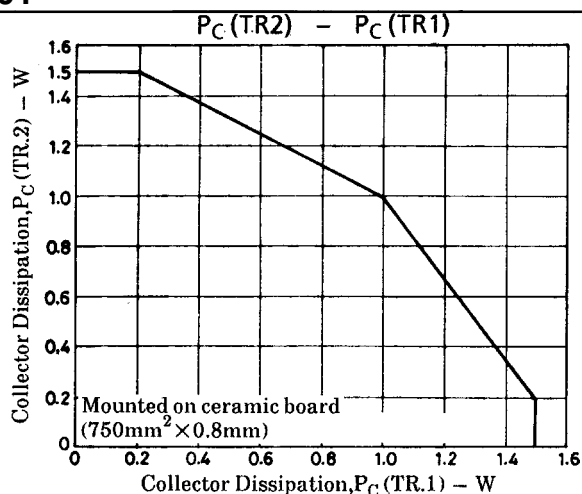
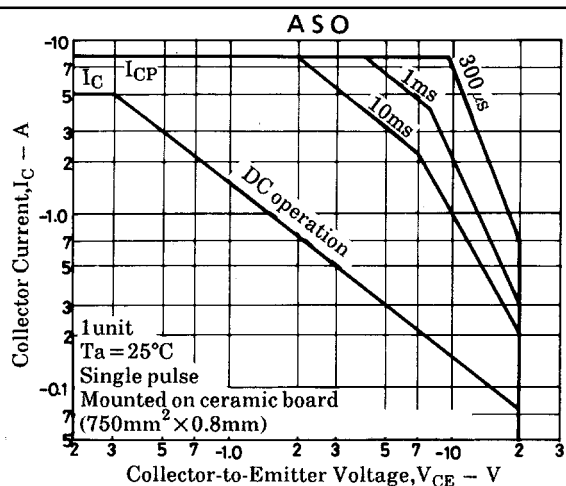
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$			-500	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-500	nA
DC Current Gain	h_{FE1}	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	140		400	
	h_{FE2}	$V_{CE}=-2\text{V}, I_C=-4\text{A}$	60			
DC Current Gain Ratio	$h_{FE}(\text{small/large})$	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	0.8			
Gain-Bandwidth Product	f_T	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$		350		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, f=1\text{MHz}$		60		pF
C-E Saturation Voltage	$V_{CE}(\text{sat})$	$I_C=-3\text{A}, I_B=-60\text{mA}$		-250	-500	mV
B-E Saturation Voltage	$V_{BE}(\text{sat})$	$I_C=-3\text{A}, I_B=-60\text{mA}$		-1.0	-1.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, R_{BE}=\infty$	-20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Turn-ON Time	t_{on}	See specified Test Circuit		40		ns
Storage Time	t_{stg}	See specified Test Circuit		200		ns
Fall Time	t_f	See specified Test Circuit		10		ns

FX501



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